Central™
Semiconductor Corp.

PROCESS CP192V

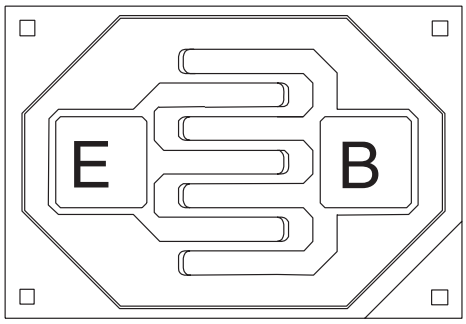
Small Signal Transistors

NPN - Amp Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	13 x 17 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.0 X 3.0 MILS
Emitter Bonding Pad Area	3.0 X 3.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



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BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

52,920

PRINCIPAL DEVICE TYPES

2N3904
CMKT3904
CMLT3904E
CMPT3904
CMST3904
CXT3904
CZT3904

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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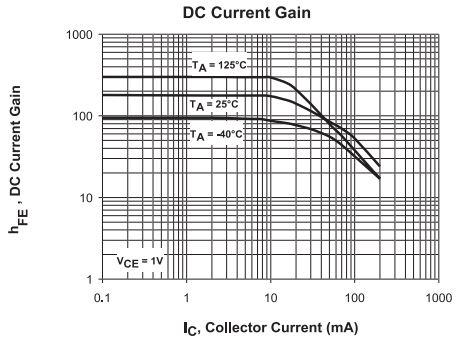
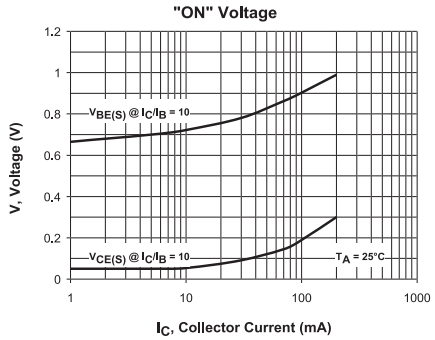
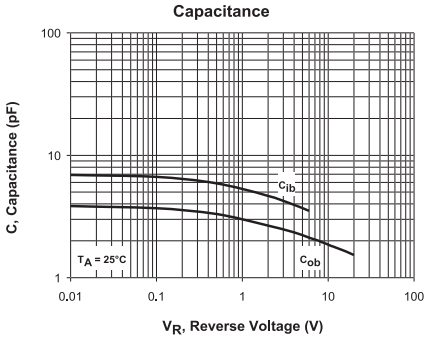
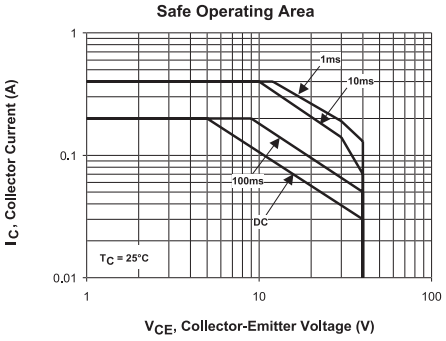
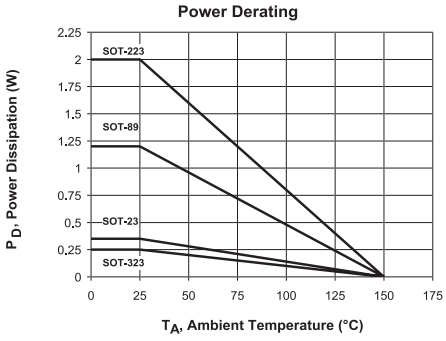
Typical Electrical Characteristics

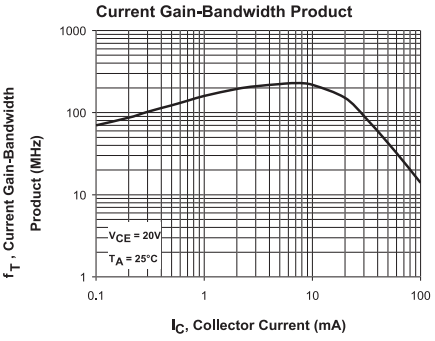












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